# Surface Mount Schottky Power Rectifier

# **SMB Power Surface Mount Package**

... employing the Schottky Barrier principle in a metal-to-silicon power rectifier. Features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency switching power supplies; free wheeling diodes and polarity protection diodes.

- Compact Package with J–Bend Leads Ideal for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guardring for Over–Voltage Protection
- Low Forward Voltage Drop

### **Mechanical Characteristics:**

- Case: Molded Epoxy
- Epoxy Meets UL94, VO at 1/8"
- Weight: 95 mg (approximately)
- Cathode Polarity Band
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Available in 12 mm Tape, 2500 Units per 13" Reel, Add "T3" Suffix to Part Number
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Marking: B14L

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	40	V	
Average Rectified Forward Current (At Rated V <sub>R</sub> , T <sub>C</sub> = 110°C)	l <sub>O</sub>	1.0	A	
Peak Repetitive Forward Current (At Rated V <sub>R</sub> , Square Wave, 100 kHz, T <sub>C</sub> = 110°C)	I <sub>FRM</sub>	2.0	A	
Non–Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	40	A	
Storage/Operating Case Temperature	T <sub>stg</sub> , T <sub>C</sub>	-55 to +150	°C	
Operating Junction Temperature	TJ	-55 to +125	°C	
Voltage Rate of Change (Rated V <sub>R</sub> , T <sub>J</sub> = 25°C)	dv/dt	10,000	V/μs	



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## SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE 40 VOLTS



SMB CASE 403A PLASTIC

### MARKING DIAGRAM



B14L = Device Code

## ORDERING INFORMATION

	Device	Package	Shipping
MB	RS140LT3	SMB	2500/Tape & Reel

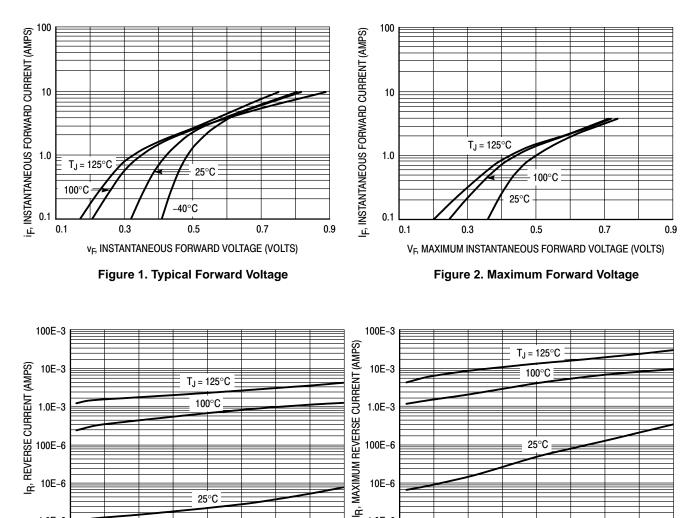
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance — Junction–to–Lead (Note 1.) Thermal Resistance — Junction–to–Ambient (Note 2.)	$R_{ heta JL} \ R_{ heta JA}$	24 80	°C/W

#### **ELECTRICAL CHARACTERISTICS**

Maximum Instantaneous Forward Voltage (Note 3.)		٧ <sub>F</sub>	T <sub>J</sub> = 25°C	T <sub>J</sub> = 125°C	Volts
see Figure 2	(i <sub>F</sub> = 1.0 A) (i <sub>F</sub> = 2.0 A)		0.5 0.6	0.425 0.58	
Maximum Instantaneous Reverse Current (Note 3.)		I <sub>R</sub>	T <sub>J</sub> = 25°C	T <sub>J</sub> = 100°C	mA
see Figure 4	(V <sub>R</sub> = 40 V) (V <sub>R</sub> = 20 V)		0.4 0.02	10 5.0	

1. Mounted with minimum recommended pad size, PC Board FR4.2. 1 inch square pad size (1 x 0.5 inch for each lead) on FR4 board.3. Pulse Test: Pulse Width  $\leq$  250 µs, Duty Cycle  $\leq$  2.0%.



100E-6

10E-6

1.0E-6 0

40

Figure 3. Typical Reverse Current

V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

25°C

20

30

100E-6

10E-6

1.0E-6

0

10



20

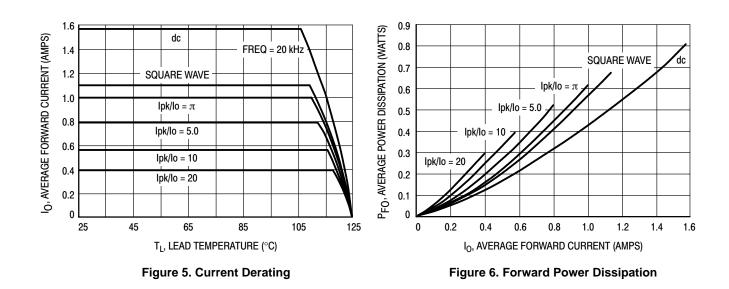
V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

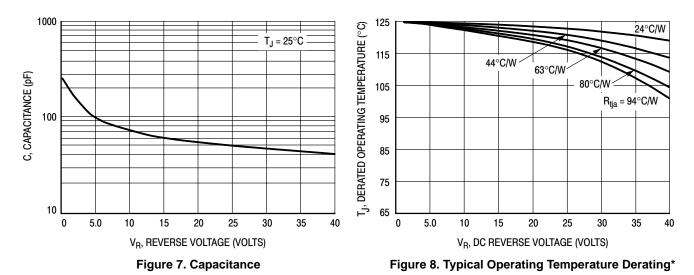
30

40

10

25°C



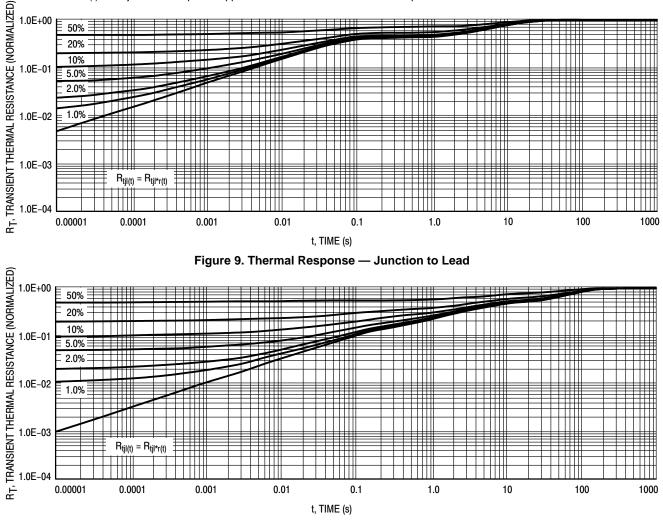


\* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of  $T_J$  therefore must include forward and reverse power effects. The allowable operating  $T_J$  may be calculated from the equation:  $T_J = T_{Jmax} - r(t)(Pf + Pr)$  where r(t) = thermal impedance under given conditions,

r(t) = thermal impedance under given conditions Pf = forward power dissipation, and

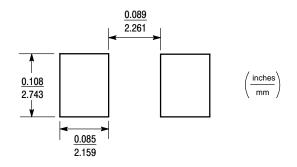
Pr = reverse power dissipation

This graph displays the derated allowable  $T_J$  due to reverse bias under DC conditions only and is calculated as  $T_J = T_{Jmax} - r(t)Pr$ , where r(t) = Rthja. For other power applications further calculations must be performed.

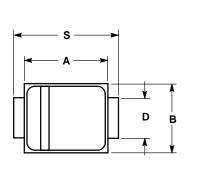


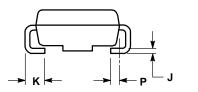


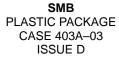
# MINIMUM SOLDER PAD SIZES

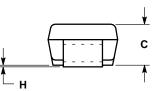


# PACKAGE DIMENSIONS









NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.160	0.180	4.06	4.57	
В	0.130	0.150	3.30	3.81	
С	0.075	0.095	1.90	2.41	
D	0.077	0.083	1.96	2.11	
Н	0.0020	0.0060	0.051	0.152	
J	0.006	0.012	0.15	0.30	
Κ	0.030	0.050	0.76	1.27	
Р	0.020 REF		0.51 REF		
S	0.205	0.220	5.21	5.59	

# <u>Notes</u>

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